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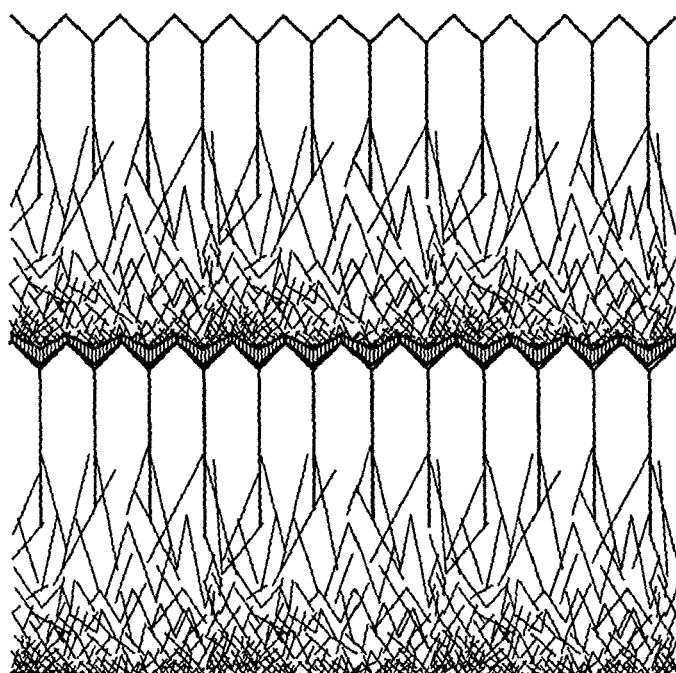
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(54) Title: DIFFERENTIAL STRESS REDUCTION IN THIN FILMS



(57) Abstract: A crystalline thin film structure formed by the deposition of a predominant first crystalline material in two or more layers interleaved by layers of a second crystalline material having a lattice constant that differs from the lattice constant of the predominant first crystalline material in order to disrupt the growth of columnar crystals in the predominant first crystalline material in order to reduce the differential stress profile through the thickness of the film structure relative to the differential stress profile of a crystalline thin film structure formed solely from the predominant first crystalline material.



WO 03/045836 A1



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